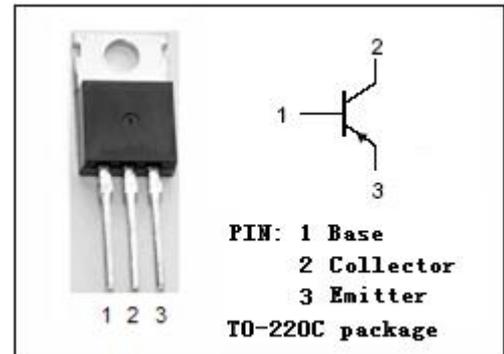


isc Silicon PNP Power Transistor
2SB1085
DESCRIPTION

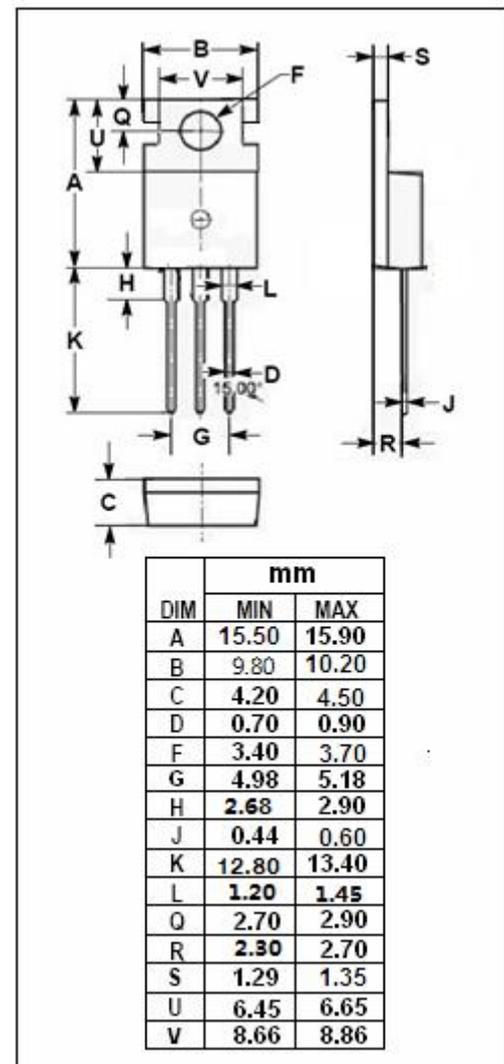
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -120V$ (Min)
- Wide Area of Safe Operation
- Complement to Type 2SD1562
- Minimum Lot-to-Lot variations for robust device performance and reliable operation


APPLICATIONS

- Designed for low frequency power amplifier applications.

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ C$)

| SYMBOL | PARAMETER | VALUE | UNIT |
|-----------|---|---------|------------|
| V_{CBO} | Collector-Base Voltage | -120 | V |
| V_{CEO} | Collector-Emitter Voltage | -120 | V |
| V_{EBO} | Emitter-Base Voltage | -5.0 | V |
| I_C | Collector Current-Continuous | -1.5 | A |
| I_{CM} | Collector Current-Peak | -3 | A |
| P_C | Total Power Dissipation @ $T_c=25^\circ C$ | 20 | W |
| | Total Power Dissipation @ $T_a=25^\circ C$ | 1.5 | |
| T_J | Junction Temperature | 150 | |
| T_{stg} | Storage Temperature Range | -55~150 | $^\circ C$ |



isc Silicon PNP Power Transistor
2SB1085
ELECTRICAL CHARACTERISTICS

 T_c=25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|--|------|------|------|------|
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage | I _C = -1mA; I _B = 0 | -120 | | | V |
| V _{(BR)CBO} | Collector-Base Breakdown Voltage | I _C = -50 μ A; I _E = 0 | -120 | | | V |
| V _{(BR)EBO} | Emitter-Base Breakdown Voltage | I _E = -50 μ A; I _C = 0 | -5 | | | V |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = -1A; I _B = -0.1A | | | -2.0 | V |
| V _{BE(sat)} | Base-Emitter Saturation Voltage | I _C = -1A; I _B = -0.1A | | | -1.5 | V |
| I _{CBO} | Collector Cutoff Current | V _{CB} = -100V; I _E = 0 | | | -1.0 | μ A |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = -4V; I _C = 0 | | | -1.0 | μ A |
| h _{FE} | DC Current Gain | I _C = -0.1A; V _{CE} = -5V | 60 | | 200 | |
| f _T | Current-Gain—Bandwidth Product | I _C = -0.1A; V _{CE} = -5V | | 50 | | MHz |
| C _{OB} | Output Capacitance | I _E = 0; V _{CB} = -10V; f _{test} = 1MHz | | 30 | | pF |

◆ h_{FE} Classifications

| D | E |
|--------|---------|
| 60-120 | 100-200 |

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